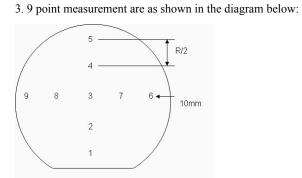
Icemos Technology Ltd Product Specification 1000.691301 Issue Date 21 June 2021 14:31:00

Part Number	Customer	

Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	647.00 +/- 26.10 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	3mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	525.00 +/- 25.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 - 50 Ohmem	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and lasermark	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and Device Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	120.00 +/- 1.00 μm	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Guaranteed by process
	25.0	Edge Removal Angle	45 +/- 15deg	Graranteed by process
	26.0	Edge Removal Depth in Handle	<100um	Guaranteed by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	1 - 10 Ohm-cm	Wafer Vendor
	30.0	Oxygen Concentration	<12.60ppma	Wafer Supplier
	31.0	Buried Layer Implant	none	implant vendor
	32.0	Voids	All wafers scanned for voids by Scanning Acoustic Microscope (SAM)	SAM & Bright Light, 100% (note 2). Void spec as per comments below.
	33.0	Scratches	0	Bright Light, 100% (note 2)
	34.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	ction performed using microscope scan as below. 5x objective.	
		spections performed exclude all wafer area outside the edge exclusive the edge exclusive and the edge exclusive area outside the edge exclusive area outside the edge exclusive and the edge exclusive area outside area.	ision defined in Overall

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.



Additional Information